



SHEET 1 OF 1

## FORM PTO - 1449

SUPPLEMENTAL INFORMATION  
DISCLOSURE STATEMENT

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APPLICANTS: Leitz *et al.*

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## U.S. PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	FILING DATE IF APPROPRIATE

## FOREIGN PATENT DOCUMENTS

EXAM. INIT.		DOCUMENT NUMBER	DATE	COUNTRY CODE	CLASS	SUB CLASS	FILING DATE	ABSTRACT ONLY	ENGLISH LANG (Y/N)
<i>Lee</i>	B52	02/13262	02/14/2002	WO				N	Y
<i>Lee</i>	B53	03/105189	12/18/2003	WO				N	Y
<i>Lee</i>	B54	0 353 423	02/07/1990	EP				N	Y
<i>Lee</i>	B55	1 014 431	06/28/2000	EP				N	N

## OTHER ART, JOURNAL ARTICLES, ETC.

EXAM. INIT.	OTHER DOCUMENTS: (Including Author, Title, Date, Relevant Pages, Place of Publication)	
<i>Lee</i>	C136	International Search Report for International Patent Application No. PCT/US03/26467, dated July 13, 2004, 3 pages.
<i>Lee</i>	C137	Luo <i>et al.</i> , "Compliant effect of low-temperature Si buffer for SiGe growth," <i>Applied Physics Letters</i> , 78(4):454-456 (2001).
<i>Lee</i>	C138	Vyatkin <i>et al.</i> , "Study of Strain Relaxation in Epitaxial Structure GE <sub>0.2</sub> Si <sub>0.8</sub> /Si At Thermo-Implantation Treatment by Ion Beam Channeling," <i>Mat. Res. Soc. Symp. Proc.</i> , 585:183-189 (2000).

EXAMINER	<i>Kevin May Lee</i>	DATE CONSIDERED
3121278-1		<i>7/26/05</i>